MITSUBISHI Nch POWER MOSFET

FS50VSJ-2

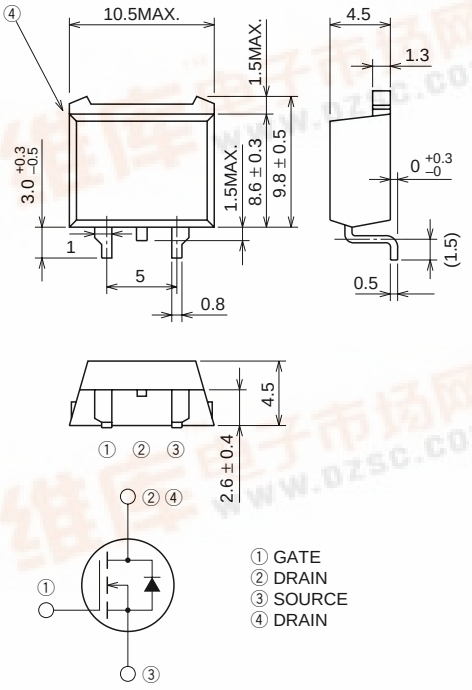
HIGH-SPEED SWITCHING USE

FS50VSJ-2

- 4V DRIVE
- VDSS 100V
- rDS (ON) (MAX) 48mΩ
- ID 50A
- Integrated Fast Recovery Diode (TYP.) 90ns

OUTLINE DRAWING

Dimensions in mm



TO-220S

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (Tc = 25°C)

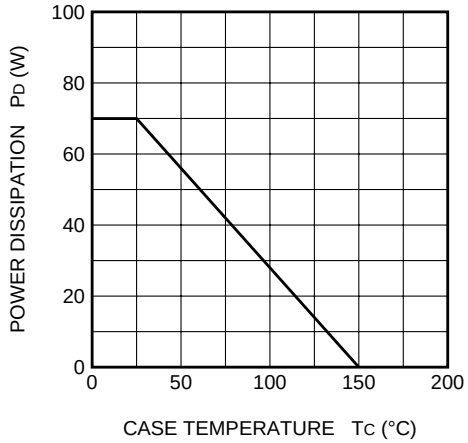
Symbol	Parameter	Conditions	Ratings	Unit
VDSS	Drain-source voltage	VGS = 0V	100	V
VGSS	Gate-source voltage	VDS = 0V	±20	V
ID	Drain current		50	A
IDM	Drain current (Pulsed)		200	A
IDA	Avalanche drain current (Pulsed)	L = 50µH	50	A
IS	Source current		50	A
ISM	Source current (Pulsed)		200	A
PD	Maximum power dissipation		70	W
Tch	Channel temperature		–55 ~ +150	°C
Tstg	Storage temperature		–55 ~ +150	°C
—	Weight	Typical value	1.2	g

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

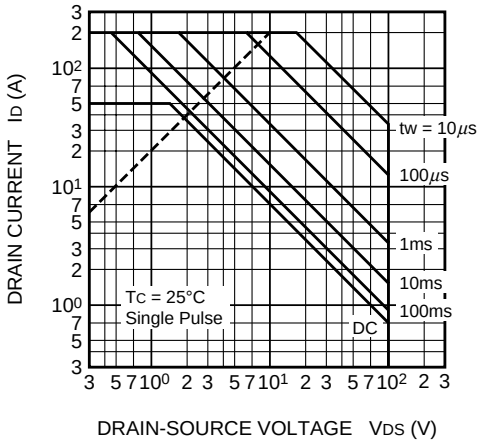
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)\ DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS} = 0V	100	—	—	V
I_{GSS}	Gate-source leakage current	V_{GS} = ±20V, V_{DS} = 0V	—	—	±0.1	μA
I_{DSS}	Drain-source leakage current	V_{DS} = 100V, V_{GS} = 0V	—	—	0.1	mA
$V_{GS\ (th)}$	Gate-source threshold voltage	I_D = 1mA, V_{DS} = 10V	1.0	1.5	2.0	V
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 25A, V_{GS} = 10V	—	37	48	mΩ
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 25A, V_{GS} = 4V	—	40	52	mΩ
$V_{DS\ (ON)}$	Drain-source on-state voltage	I_D = 25A, V_{GS} = 10V	—	0.93	1.20	V
$\lvert y_{fs} \rvert$	Forward transfer admittance	I_D = 25A, V_{DS} = 10V	—	40	—	S
C_{iss}	Input capacitance	V_{DS} = 10V, V_{GS} = 0V, f = 1MHz	—	3000	—	pF
C_{oss}	Output capacitance		—	410	—	pF
C_{rss}	Reverse transfer capacitance		—	210	—	pF
$t_{d\ (on)}$	Turn-on delay time	V_{DD} = 50V, I_D = 25A, V_{GS} = 10V, R_{GEN} = R_{GS} = 50Ω	—	22	—	ns
t_r	Rise time		—	65	—	ns
$t_{d\ (off)}$	Turn-off delay time		—	270	—	ns
t_f	Fall time		—	160	—	ns
V_{SD}	Source-drain voltage	I_S = 25A, V_{GS} = 0V	—	1.0	1.5	V
$R_{th\ (ch-c)}$	Thermal resistance	Channel to case	—	—	1.78	°C/W
t_{rr}	Reverse recovery time	I_S = 50A, dis/dt = –100A/μs	—	90	—	ns

PERFORMANCE CURVES

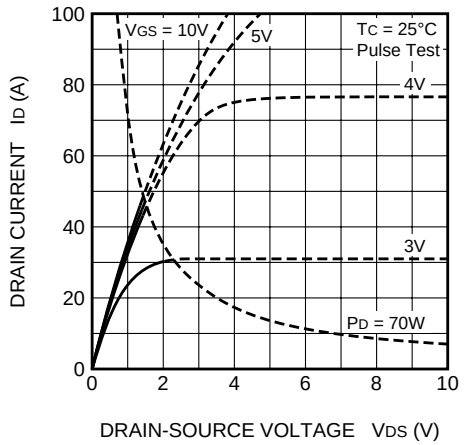
POWER DISSIPATION DERATING CURVE



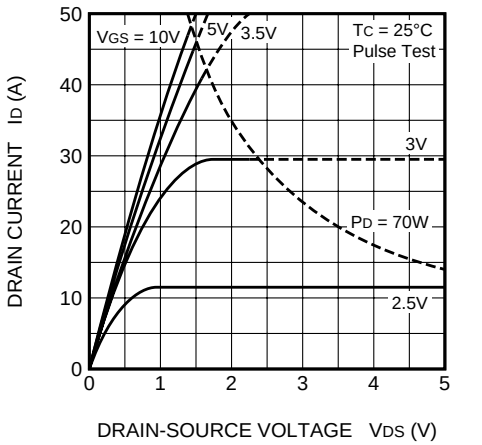
MAXIMUM SAFE OPERATING AREA



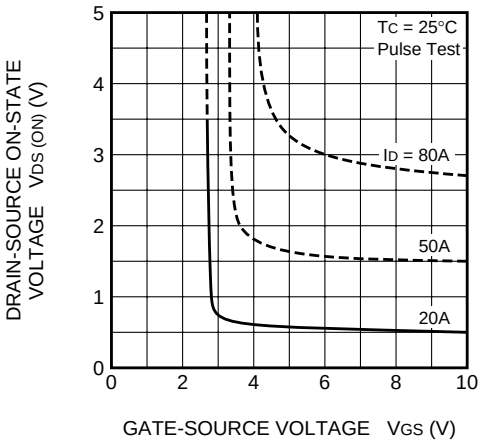
OUTPUT CHARACTERISTICS (TYPICAL)



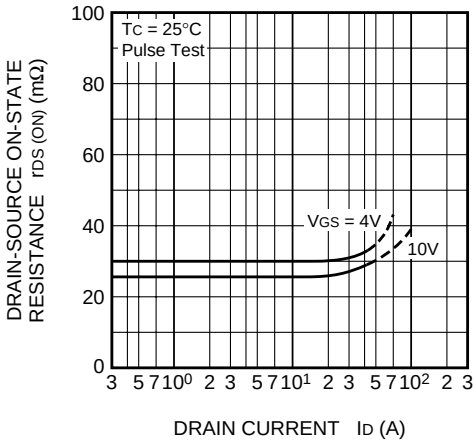
OUTPUT CHARACTERISTICS (TYPICAL)



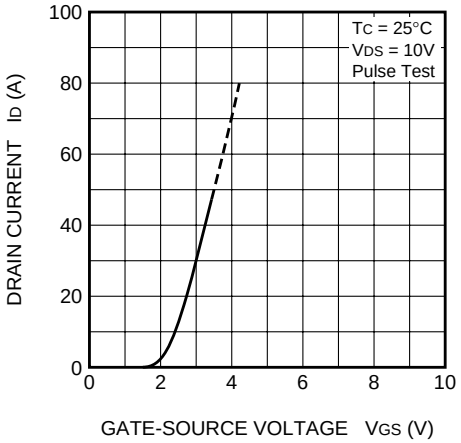
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



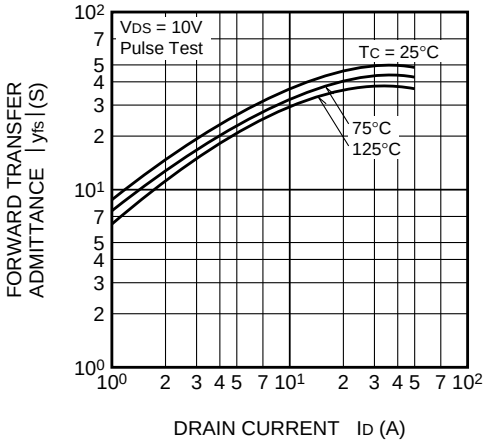
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



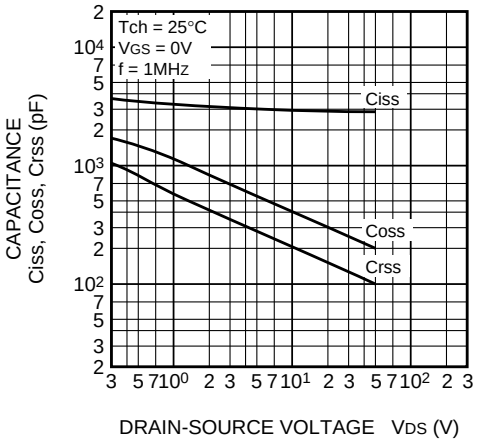
TRANSFER CHARACTERISTICS (TYPICAL)



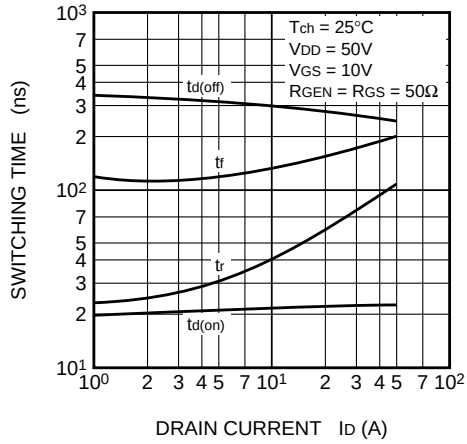
FORWARD TRANSFER ADMITTANCE VS.DRAIN CURRENT (TYPICAL)



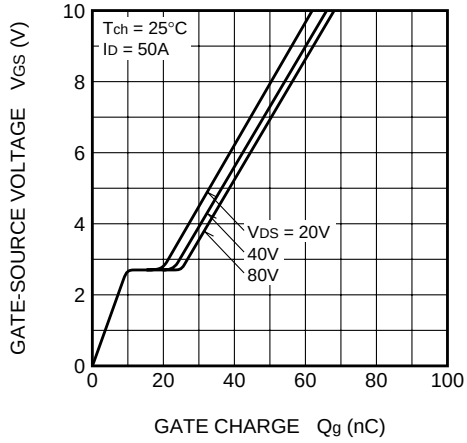
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



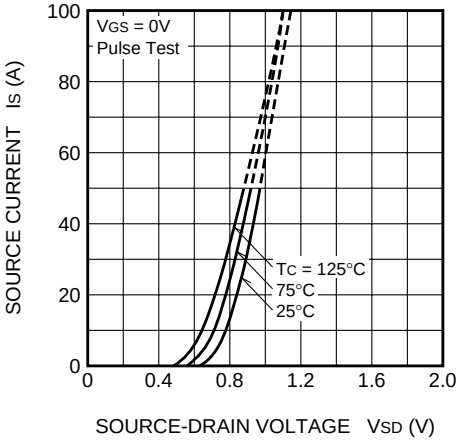
SWITCHING CHARACTERISTICS (TYPICAL)



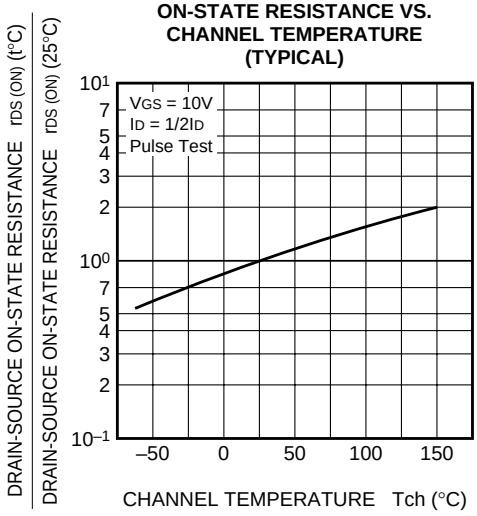
GATE-SOURCE VOLTAGE VS.GATE CHARGE (TYPICAL)



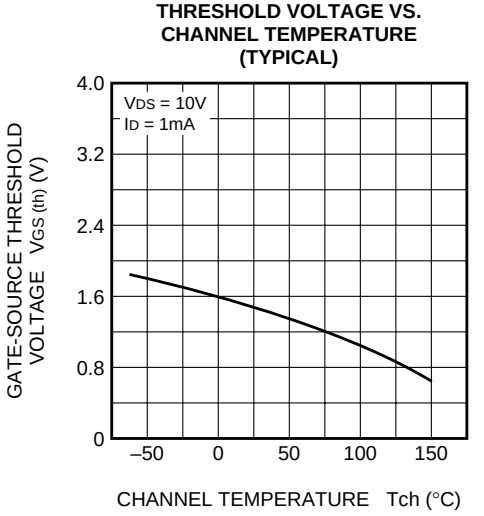
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



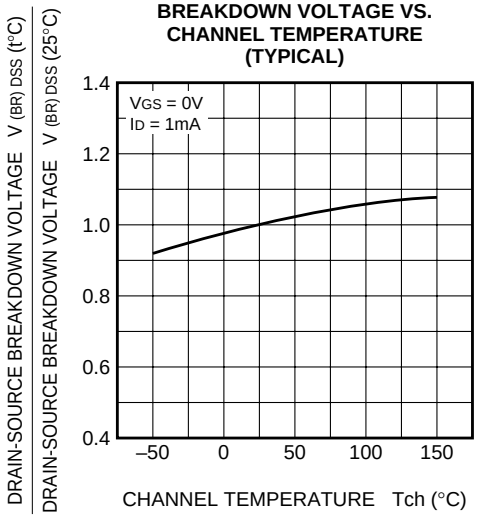
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS